

Katsumi Kishino

List of Publications by Year in descending order

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153
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times ranked

2111
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Emission color control from blue to red with nanocolumn diameter of InGaN/GaN nanocolumn arrays grown on same substrate. Applied Physics Letters, 2010, 96, . | 1.5 | 359 |
| 2 | InGaN/GaN Multiple Quantum Disk Nanocolumn Light-Emitting Diodes Grown on (111) Si Substrate. Japanese Journal of Applied Physics, 2004, 43, L1524-L1526. | 0.8 | 351 |
| 3 | Growth of Self-Organized GaN Nanostructures on $\text{Al}_2\text{O}_3(0001)$ by RF-Radical Source Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1997, 36, L459-L462. | 0.8 | 341 |
| 4 | Improved Ti-mask selective-area growth (SAG) by rf-plasma-assisted molecular beam epitaxy demonstrating extremely uniform GaN nanocolumn arrays. Journal of Crystal Growth, 2009, 311, 2063-2068. | 0.7 | 254 |
| 5 | Ti-mask Selective-Area Growth of GaN by RF-Plasma-Assisted Molecular-Beam Epitaxy for Fabricating Regularly Arranged InGaN/GaN Nanocolumns. Applied Physics Express, 0, 1, 124002. | 1.1 | 179 |
| 6 | Intersubband transition in $(\text{GaN})_m/(\text{AlN})_n$ superlattices in the wavelength range from 1.08 to 1.61 μm . Applied Physics Letters, 2002, 81, 1234-1236. | 1.5 | 167 |
| 7 | Selective-area growth of GaN nanocolumns on Si(111) substrates for application to nanocolumn emitters with systematic analysis of dislocation filtering effect of nanocolumns. Nanotechnology, 2015, 26, 225602. | 1.3 | 130 |
| 8 | Monolithic Integration of InGaN-Based Nanocolumn Light-Emitting Diodes with Different Emission Colors. Applied Physics Express, 2013, 6, 012101. | 1.1 | 116 |
| 9 | Self-organization of GaN/Al _{0.18} Ga _{0.82} N multi-layer nano-columns on (0001) Al ₂ O ₃ by RF molecular beam epitaxy for fabricating GaN quantum disks. Journal of Crystal Growth, 1998, 189-190, 138-141. | 0.7 | 96 |
| 10 | InGaN/GaN nanocolumn LEDs emitting from blue to red. , 2007, , . | | 94 |
| 11 | Strain relaxation effect by nanotexturing InGaN/GaN multiple quantum well. Journal of Applied Physics, 2010, 107, . | 1.1 | 93 |
| 12 | Origin of high oscillator strength in green-emitting InGa ^x N ^{1-x} /GaN nanocolumns. Applied Physics Letters, 2006, 89, 163124. | 1.5 | 92 |
| 13 | Ultrafast intersubband relaxation and nonlinear susceptibility at 1.55 μm in GaN/AlN multiple-quantum wells. Applied Physics Letters, 2004, 84, 1102-1104. | 1.5 | 91 |
| 14 | Optical properties of InGaN/GaN nanopillars fabricated by postgrowth chemically assisted ion beam etching. Journal of Applied Physics, 2010, 107, . | 1.1 | 88 |
| 15 | Enhanced carrier confinement effect by the multiquantum barrier in 660 nm GaInP/AlInP visible lasers. Applied Physics Letters, 1991, 58, 1822-1824. | 1.5 | 80 |
| 16 | Structural and optical properties of GaN nanocolumns grown on (0001) sapphire substrates by rf-plasma-assisted molecular-beam epitaxy. Journal of Crystal Growth, 2007, 300, 259-262. | 0.7 | 80 |
| 17 | GaN/AlGaIn nanocolumn ultraviolet light-emitting diodes grown on n-(111) Si by RF-plasma-assisted molecular beam epitaxy. Electronics Letters, 2008, 44, 151. | 0.5 | 63 |
| 18 | Monolithic integration of four-colour InGa ^x N ^{1-x} -based nanocolumn LEDs. Electronics Letters, 2015, 51, 852-854. | 0.5 | 61 |

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 19 | Two-dimensional multicolor (RGBY) integrated nanocolumn micro-LEDs as a fundamental technology of micro-LED display. Applied Physics Express, 2020, 13, 014003. | 1.1 | 59 |
| 20 | Stimulated emission from GaN nanocolumns. Physica Status Solidi (B): Basic Research, 2004, 241, 2754-2758. | 0.7 | 52 |
| 21 | Lattice parameters, deviations from Vegard's rule, and E2 phonons in InAlN. Applied Physics Letters, 2008, 93, . | 1.5 | 44 |
| 22 | Optically Pumped Green (530-560 nm) Stimulated Emissions from InGaN/GaN Multiple-Quantum-Well Triangular-Lattice Nanocolumn Arrays. Applied Physics Express, 2011, 4, 055001. | 1.1 | 42 |
| 23 | Refractive indices measurement of (GaInP) _m /(AlInP) _n quasi-ternaries and GaInP/AlInP multiple quantum wells. Journal of Applied Physics, 1994, 76, 1809-1818. | 1.1 | 40 |
| 24 | Ultraviolet GaN-based nanocolumn light-emitting diodes grown on (111) Si substrates by rf-plasma-assisted molecular beam epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1067-1069. | 0.8 | 40 |
| 25 | Dislocation reduction via selective-area growth of InN accompanied by lateral growth by rf-plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2010, 97, . | 1.5 | 40 |
| 26 | GaN/AlGaIn Nanocolumn Ultraviolet Light-Emitting Diode Using Double-Layer Graphene as Substrate and Transparent Electrode. Nano Letters, 2019, 19, 1649-1658. | 4.5 | 39 |
| 27 | Positive binding energy of a biexciton confined in a localization center formed in a single disk. Physical Review B, 2009, 79, . | 1.1 | 38 |
| 28 | Selective-Area Growth of GaN Nanocolumns on Si(111) Substrates Using Nitrided Al Nanopatterns by RF-Plasma-Assisted Molecular-Beam Epitaxy. Applied Physics Express, 2008, 1, 015006. | 1.1 | 37 |
| 29 | Directional radiation beam from yellow-emitting InGaIn-based nanocolumn LEDs with ordered bottom-up nanocolumn array. Applied Physics Express, 2014, 7, 112102. | 1.1 | 37 |
| 30 | Green-Light Nanocolumn Light Emitting Diodes With Triangular-Lattice Uniform Arrays of InGaIn-Based Nanocolumns. IEEE Journal of Quantum Electronics, 2014, 50, 538-547. | 1.0 | 37 |
| 31 | Yellow-green ZnCdSe/BeZnTe II-VI laser diodes grown on InP substrates. Applied Physics Letters, 2002, 81, 972-974. | 1.5 | 36 |
| 32 | Molecular beam epitaxial growth of MgZnCdSe on (100) InP substrates. Journal of Electronic Materials, 1996, 25, 425-430. | 1.0 | 35 |
| 33 | Selective growth of GaN nanocolumns by Al thin layer on substrate. Physica Status Solidi (B): Basic Research, 2007, 244, 1815-1819. | 0.7 | 29 |
| 34 | High structural quality In _{0.75} Ga _{0.25} N multiple quantum wells grown by molecular beam epitaxy. Applied Physics Letters, 2006, 89, 041907. | 1.5 | 26 |
| 35 | 600-nm wavelength range GaInP/AlInP quasi-ternary compounds and lasers prepared by gas-source molecular-beam epitaxy. Journal of Applied Physics, 1993, 74, 819-824. | 1.1 | 25 |
| 36 | 633 nm Red Emissions from InGaIn Nanocolumn Light-Emitting Diode by Radio Frequency Plasma Assisted Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2013, 52, 08JE18. | 0.8 | 25 |

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|----|--|-----|-----------|
| 37 | Novel selective area growth (SAG) method for regularly arranged AlGaIn nanocolumns using nanotemplates. <i>Journal of Crystal Growth</i> , 2015, 425, 316-321. | 0.7 | 25 |
| 38 | Visible Light Emitting Diode with ZnCdSe/BeZnTe Superlattices as an Active Layer and MgSe/BeZnTe Superlattices as a p-Cladding Layer. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 229, 1001-1004. | 0.7 | 24 |
| 39 | Selective area growth of InGaIn-based nanocolumn LED crystals on AlN/Si substrates useful for integrated λ -LED fabrication. <i>Applied Physics Letters</i> , 2018, 112, . | 1.5 | 23 |
| 40 | High-quality GaInP and GaInP/AlInP double heterostructure lasers grown on GaAs substrates by gas-source molecular beam epitaxy. <i>Journal of Applied Physics</i> , 1989, 66, 4557-4559. | 1.1 | 22 |
| 41 | Self-organization of dislocation-free, high-density, vertically aligned GaN nanocolumns involving InGaIn quantum wells on graphene/SiO ₂ covered with a thin AlN buffer layer. <i>Nanotechnology</i> , 2016, 27, 055302. | 1.3 | 22 |
| 42 | Remarkable reduction of threshold current density by substrate misorientation effects in 660 nm visible light lasers with GaInP bulk active layers. <i>Applied Physics Letters</i> , 1992, 60, 1046-1048. | 1.5 | 21 |
| 43 | AlGaIn Resonant Tunneling Diodes Grown by rf-MBE. <i>Physica Status Solidi A</i> , 2001, 188, 187-190. | 1.7 | 21 |
| 44 | Vertical GaN nanocolumns grown on graphene intermediated with a thin AlN buffer layer. <i>Nanotechnology</i> , 2019, 30, 015604. | 1.3 | 21 |
| 45 | Photopumped green lasing on BeZnSeTe double heterostructures grown on InP substrates. <i>Applied Physics Letters</i> , 2009, 94, 021104. | 1.5 | 19 |
| 46 | GaN nanocolumn arrays with diameter $\leq 30\text{Å}$nm prepared by two-step selective area growth. <i>Electronics Letters</i> , 2015, 51, 2125-2126. | 0.5 | 19 |
| 47 | Growth study of self-assembled GaN nanocolumns on silica glass by plasma assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2017, 480, 67-73. | 0.7 | 19 |
| 48 | Refractive index measurements of MgZnCdSe II-VI compound semiconductors grown on InP substrates and fabrications of 500-600 nm range MgZnCdSe distributed Bragg reflectors. <i>Journal of Applied Physics</i> , 1997, 81, 7575-7579. | 1.1 | 18 |
| 49 | Formation of InGaIn quantum dots in regularly arranged GaN nanocolumns grown by rf-plasma-assisted molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010, 7, 2374-2377. | 0.8 | 18 |
| 50 | Carrier-density dependence of photoluminescence from localized states in InGaIn/GaN quantum wells in nanocolumns and a thin film. <i>Journal of Applied Physics</i> , 2015, 118, . | 1.1 | 17 |
| 51 | Lasing Actions in GaN Tiny Hexagonal Nanoring Resonators. <i>IEEE Photonics Journal</i> , 2010, 2, 1027-1033. | 1.0 | 16 |
| 52 | Photoluminescence Behaviors of Orange-Light-Emitting InGaIn-Based Nanocolumns Exhibiting High Internal Quantum Efficiency (17-22%). <i>Japanese Journal of Applied Physics</i> , 2013, 52, 08JD09. | 0.8 | 16 |
| 53 | Influence of GaN column diameter on structural properties for InGaIn nanocolumns grown on top of GaN nanocolumns. <i>AIP Advances</i> , 2016, 6, . | 0.6 | 16 |
| 54 | ZnCdTe/ZnTe Light Emitting Diodes with CdSe n-Type Contact Layers Grown on ZnTe Substrates by Molecular Beam Epitaxy. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 229, 991-994. | 0.7 | 15 |

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|----|--|-----|-----------|
| 55 | High-speed GaN growth and compositional control of GaN-AlGaN superlattice quasi-ternary compounds by RF-radical source molecular beam epitaxy. IEEE Journal of Selected Topics in Quantum Electronics, 1998, 4, 550-556. | 1.9 | 14 |
| 56 | Resonant-Cavity-Enhanced UV Metal-Semiconductor-Metal (MSM) Photodetectors Based on AlGaIn System. Physica Status Solidi A, 2001, 188, 321-324. | 1.7 | 14 |
| 57 | Characterization of ZnCdSeTe/MgZnSeTe materials for ZnTe-based visible optical devices. Physica Status Solidi (B): Basic Research, 2004, 241, 483-486. | 0.7 | 14 |
| 58 | Long life operations over 5000 hours of BeZnSeTe/MgZnCdSe visible light emitting diodes on InP substrates. Physica Status Solidi (B): Basic Research, 2006, 243, 924-928. | 0.7 | 14 |
| 59 | Fabrication and lasing characteristics of 0.67 μ m GaInAsP/AlGaAs visible lasers prepared by liquid phase epitaxy on. IEEE Journal of Quantum Electronics, 1987, 23, 180-187. | 1.0 | 13 |
| 60 | Well-arranged novel InGaIn hexagonal nanoplates at the tops of nitrogen-polarity GaN nanocolumn arrays. AIP Advances, 2012, 2, . | 0.6 | 13 |
| 61 | Proposal of a novel BeZnSeTe quaternary for II-VI middle range visible light emitting devices on InP substrates. Physica Status Solidi (B): Basic Research, 2004, 241, 747-750. | 0.7 | 11 |
| 62 | Self-Organized Eu-Doped GaN Nanocolumn Light-Emitting Diode Grown by RF-Molecular-Beam Epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2018, 216, 1800501. | 0.8 | 11 |
| 63 | Raman Scattering in GaN Nanocolumns and GaN/AlN Multiple Quantum Disk Nanocolumns. E-Journal of Surface Science and Nanotechnology, 2006, 4, 227-232. | 0.1 | 11 |
| 64 | Improved Responsivity of AlGaIn-Based Resonant Cavity-Enhanced UV Photodetectors Grown on Sapphire by RF-MBE. Physica Status Solidi A, 2002, 192, 292-295. | 1.7 | 10 |
| 65 | Low-temperature photoluminescence studies of In-rich InAlN nanocolumns. Physica Status Solidi - Rapid Research Letters, 2012, 6, 123-125. | 1.2 | 10 |
| 66 | Spectrally-broadened multimode lasing based on structurally graded InGaIn nanocolumn photonic crystals suitable for reduction of speckle contrast. Applied Physics Letters, 2016, 109, . | 1.5 | 10 |
| 67 | Novel II-VI Light Emitting Diodes Fabricated on InP Substrates Applying Wide-Gap and Highly p-Dopable BeZnTe for p-Cladding Layers. Physica Status Solidi A, 2000, 180, 37-43. | 1.7 | 9 |
| 68 | Refractive Index Measurements of BeZnTe and Related Superlattices on InP and Application for Waveguide Analysis of MgZnCdSe/BeZnTe Visible Lasers. Physica Status Solidi (B): Basic Research, 2002, 229, 987-990. | 0.7 | 9 |
| 69 | Growth and characterization of InGaIn double heterostructures for optical devices at 1.5 μ m-1.7 μ m communication wavelengths. Physica Status Solidi A, 2004, 201, 2850-2854. | 1.7 | 9 |
| 70 | Yellow-green emitters based on beryllium-chalcogenides on InP substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 1477-1486. | 0.8 | 9 |
| 71 | Complex strain distribution in individual faceted InGaIn/GaN nano-columnar heterostructures. Optical Materials Express, 2013, 3, 47. | 1.6 | 9 |
| 72 | Enhancement of light emission and internal quantum efficiency in orange and red regions for regularly arrayed InGaIn/GaN nanocolumns due to surface plasmon coupling. Applied Physics Letters, 2017, 111, . | 1.5 | 9 |

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|----|--|-----|-----------|
| 73 | Fabrication and optical properties of regularly arranged GaN-based nanocolumns on Si substrate. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2019, 37, 031207. | 0.6 | 9 |
| 74 | Column diameter dependence of the strain relaxation effect in GaN/AlGaIn quantum wells on GaN nanocolumn arrays. <i>Applied Physics Express</i> , 2019, 12, 125001. | 1.1 | 9 |
| 75 | Epitaxial lateral overgrowth of InN by rf-plasma-assisted molecular-beam epitaxy. <i>AIP Advances</i> , 2011, 1, 042145. | 0.6 | 8 |
| 76 | Photoluminescence properties of selectively grown InN microcrystals. <i>Physica Status Solidi - Rapid Research Letters</i> , 2012, 6, 157-159. | 1.2 | 8 |
| 77 | Confinement of Optical Phonons Observed by Raman Scattering in GaN/AlN Multiple Quantum Disk Nanocolumns. <i>Journal of the Physical Society of Japan</i> , 2013, 82, 014604. | 0.7 | 8 |
| 78 | Surface Phonons Studied by Raman Scattering in GaN Nanostructures. <i>Journal of the Physical Society of Japan</i> , 2017, 86, 074602. | 0.7 | 8 |
| 79 | The influence of AlN buffer layer on the growth of self-assembled GaN nanocolumns on graphene. <i>Scientific Reports</i> , 2020, 10, 853. | 1.6 | 8 |
| 80 | Self-organization mechanism of GaInP quantum wires in (GaP) _m /(InP) _m short-period binary superlattices for GaInP/AlInP multi-quantum-wire (MQWR) lasers. <i>Optical and Quantum Electronics</i> , 1996, 28, 547-556. | 1.5 | 7 |
| 81 | Intersubband Absorption at 1.2-1.6 μ m in GaN/AlN Multiple Quantum Wells Grown by rf-Plasma Molecular Beam Epitaxy. <i>Physica Status Solidi A</i> , 2002, 192, 124-128. | 1.7 | 7 |
| 82 | Aging characteristics of InGaN yellow light emitting diodes with beryllium chalcogenide (BeZnSeTe) active layers on InP substrates. <i>Physica Status Solidi A</i> , 2004, 201, 2708-2711. | 1.7 | 7 |
| 83 | Room temperature operation of 1.55 μ m wavelength-range GaN/AlN quantum well intersubband photodetectors. <i>IEICE Electronics Express</i> , 2005, 2, 566-571. | 0.3 | 7 |
| 84 | Flip-chip bonding and fabrication of well-ordered nanocolumn arrays on sputter-deposited AlN/Si (111) substrate. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015, 212, 992-996. | 0.8 | 7 |
| 85 | Photon correlation study of background suppressed single InGaIn nanocolumns. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 04EK03. | 0.8 | 7 |
| 86 | MgZnCdSe/BeZnTe Visible Light-Emitting Diode with Longer Device Lifetime over 1000 h. <i>Physica Status Solidi A</i> , 2002, 192, 201-205. | 1.7 | 6 |
| 87 | Development of yellow-green LEDs and LDs using MgZnCdSe-BeZnTe superlattices on InP substrates by MBE. <i>Physica Status Solidi (B): Basic Research</i> , 2004, 241, 739-746. | 0.7 | 6 |
| 88 | Growth of high-In-content InGaIn multiple quantum disk nanocolumns on Si(111) by RF plasma-assisted molecular-beam epitaxy. <i>Physica Status Solidi (B): Basic Research</i> , 2006, 243, 1481-1485. | 0.7 | 6 |
| 89 | Effect of Be-doping on InGaIn/GaN nanocolumn light-emitting diode structures by rf-plasma-assisted molecular-beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 3069-3072. | 0.8 | 6 |
| 90 | Whispering gallery mode in periodic InGaIn-based hexagonal nanoring arrays grown by rf-MBE using Ti-mask selective-area growth. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010, 207, 37-40. | 0.8 | 6 |

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| 91 | Thermally Engineered Flip-Chip InGaN/GaN Well-Ordered Nanocolumn Array LEDs. IEEE Photonics Technology Letters, 2015, 27, 2343-2346. | 1.3 | 6 |
| 92 | Crystal structure and optical properties of a high-density InGaN nanoumbrella array as a white light source without phosphors. NPG Asia Materials, 2016, 8, e289-e289. | 3.8 | 6 |
| 93 | Stable wavelength operation of europium-doped GaN nanocolumn light-emitting diodes grown by rf-plasma-assisted molecular beam epitaxy. Electronics Letters, 2017, 53, 666-668. | 0.5 | 6 |
| 94 | Red-Emitting InGaN-Based Nanocolumn Light-Emitting Diodes with Highly Directional Beam Profiles. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900771. | 0.8 | 6 |
| 95 | Graphene-Based Transparent Conducting Substrates for GaN/AlGaIn Nanocolumn Flip-Chip Ultraviolet Light-Emitting Diodes. ACS Applied Nano Materials, 2021, 4, 9653-9664. | 2.4 | 6 |
| 96 | Monolithically integrated green-to-orange color InGaN-based nanocolumn photonic crystal LEDs with directional radiation beam profiles. Applied Physics Express, 2022, 15, 022013. | 1.1 | 6 |
| 97 | Reduction of Defect Density of ZnCdSe on InP Substrates by Introducing BeZnTe Buffer Layers. Physica Status Solidi (B): Basic Research, 2002, 229, 107-110. | 0.7 | 5 |
| 98 | Yellow-green lasing operations of ZnCdTe/MgZnSeTe laser diodes on ZnTe substrates. Physica Status Solidi (B): Basic Research, 2006, 243, 955-958. | 0.7 | 5 |
| 99 | Investigation of p-side contact layers for II-VI compound semiconductor optical devices fabricated on InP substrates by MBE. Journal of Crystal Growth, 2015, 425, 199-202. | 0.7 | 5 |
| 100 | Energy- and density-dependent dynamics of photoexcited carriers in InN films. Applied Physics Letters, 2009, 95, . | 1.5 | 4 |
| 101 | Optical properties of InGaN/GaN nanocolumns in yellow-to-red region. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 2477-2480. | 0.8 | 4 |
| 102 | Optical properties of arrays of hexagonal GaN microdisks acting as whispering-gallery-mode-type optical microcavities. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1017-1020. | 0.8 | 4 |
| 103 | Spatial emission distribution and carrier recombination dynamics in regularly arrayed InGaN/GaN quantum structure nanocolumns. Japanese Journal of Applied Physics, 2016, 55, 105001. | 0.8 | 4 |
| 104 | Effect of structural properties on optical characteristics of InGaN/GaN nanocolumns fabricated by selective-area growth. Applied Physics Express, 2017, 10, 045001. | 1.1 | 4 |
| 105 | Photonic band characterization in InGaN/GaN nanocolumn arrays with triangular and honeycomb lattices by angle-resolved micro-photoluminescence measurements. Japanese Journal of Applied Physics, 2021, 60, 060904. | 0.8 | 4 |
| 106 | Energy diagram and parameters regarding localized states in InGaN/GaN nanocolumns. Journal of Applied Physics, 2021, 130, . | 1.1 | 4 |
| 107 | Self-Organized GaN/AlN Superlattice Nanocolumn Crystals Grown by RF-MBE. Materials Research Society Symposia Proceedings, 2004, 831, 666. | 0.1 | 3 |
| 108 | High p-type doping level of MgZnCdSe on InP substrates by inserting ZnTe thin layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 857-860. | 0.8 | 3 |

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|-----|--|-----|-----------|
| 109 | Selective growth of GaN nanocolumns on predeposited Al patterns by rf-plasma-assisted molecular-beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 1879-1882. | 0.8 | 3 |
| 110 | Ti-mask selective-area growth of GaN nanorings by RF-plasma-assisted molecular-beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, S607. | 0.8 | 3 |
| 111 | Investigation of yellow/green II-VI compound semiconductor laser diode structures on InP substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016, 13, 669-672. | 0.8 | 3 |
| 112 | Carrier density dependence of localized carrier recombination dynamics in orange-emitting InGaN/GaN nanocolumns. <i>Journal of Applied Physics</i> , 2020, 128, 133102. | 1.1 | 3 |
| 113 | Breakdown of the Selection Rule of Raman Spectra in a Single GaN Nanocolumn. <i>E-Journal of Surface Science and Nanotechnology</i> , 2012, 10, 321-324. | 0.1 | 3 |
| 114 | Room temperature CW operation of GaInP/AlGaInP multiple quantum wire visible lasers (MQWR-LD). , 0, , . | | 2 |
| 115 | Suppression of Inversion Domains and Decrease of Threading Dislocations in Migration Enhanced Epitaxial GaN by RF-Molecular Beam Epitaxy. <i>Physica Status Solidi A</i> , 2000, 180, 65-71. | 1.7 | 2 |
| 116 | Room temperature negative differential resistance in AlN/GaN double barrier resonant tunneling diodes grown by RF-plasma assisted molecular beam epitaxy. , 0, , . | | 2 |
| 117 | Fundamental optical properties of InN grown by epitaxial lateral overgrowth method. , 2013, , . | | 2 |
| 118 | Two-photon absorption induced anti-Stokes emission in single InGaN/GaN quantum-dot-like objects. <i>Physica Status Solidi - Rapid Research Letters</i> , 2013, 7, 344-347. | 1.2 | 2 |
| 119 | Investigation of p-contact layers for BeZnSeTe/MgZnCdSe optical devices on InP substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014, 11, 1273-1277. | 0.8 | 2 |
| 120 | Periodic Radiation Patterns and Circulating Direction of Lasing Light by Quasi Whispering Gallery Mode in Hexagonal GaN Microdisk. <i>Journal of the Physical Society of Japan</i> , 2016, 85, 053401. | 0.7 | 2 |
| 121 | Independent drive of integrated multicolor (RGBY) micro-LED array using regularly arrayed InGaN based nanocolumns. , 2017, , . | | 2 |
| 122 | Substrate Misorientation, Multi-Quantum-Barrier, and Thermal Annealing Effects in MgZnSse and ZnCdSe Compounds and Blue-Green II-VI Light Emitting Devices. <i>Physica Status Solidi (B): Basic Research</i> , 1995, 187, 327-335. | 0.7 | 1 |
| 123 | All-optical modulation using intersubband transitions at 1.55 μ m in GaN/AlN multiple quantum well. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005, 2, 2748-2752. | 0.8 | 1 |
| 124 | Highly efficient blue to red emissions of InGaN/GaN nano-disks integrated into GaN nanocolumns. , 2005, , . | | 1 |
| 125 | Lasing operation of ZnTe based yellow-green laser diodes. , 2005, , . | | 1 |
| 126 | Proposal of BeZnSeTe/MgZnCdSe II-VI compound semiconductors on InP substrates for green laser diodes. , 2008, , . | | 1 |

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|-----|--|-----|-----------|
| 127 | Exciton and biexciton properties in GaN nanocolumn: dependence on morphology and diameter. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 141-143. | 0.8 | 1 |
| 128 | Raman Scattering from a Surface Phonon in GaN Nanowalls and Regularly-Arrayed GaN Nanocolumns. , 2011, , . | | 1 |
| 129 | Raman scattering from surface phonons in GaN nanostructures. , 2013, , . | | 1 |
| 130 | Wide-range visible luminescence of ZnCdSe/BeZnTe type-II superlattices grown on InP substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1213-1217. | 0.8 | 1 |
| 131 | Switching of whispering gallery mode in hexagonal GaN microdisk by change in condition of reflection surface. Electronics Letters, 2015, 51, 170-172. | 0.5 | 1 |
| 132 | Effects of Introduction of InGaN Quantum Structures on Structural and Optical Properties of InGaN Nanocolumns. Physica Status Solidi (B): Basic Research, 2018, 255, 1700481. | 0.7 | 1 |
| 133 | Comparison of surface plasmon polariton characteristics of Ag- and Au-based InGaN/GaN nanocolumn plasmonic crystals. Applied Physics Express, 2021, 14, 105002. | 1.1 | 1 |
| 134 | ZnCdTe/ZnTe Light Emitting Diodes with CdSe n-Type Contact Layers Grown on ZnTe Substrates by Molecular Beam Epitaxy. Physica Status Solidi (B): Basic Research, 2002, 229, 991-994. | 0.7 | 1 |
| 135 | AlGaIn Resonant Tunneling Diodes Grown by rf-MBE. Physica Status Solidi A, 2001, 188, 187-190. | 1.7 | 1 |
| 136 | Substrate Misorientation Effect On Cubic And Hexagonal GaN Grown On GaAs By Molecular Beam Epitaxy Using RF-radical Nitrogen Source. , 0, , . | | 0 |
| 137 | Molecular beam epitaxial growth of MgZnCdSe on (100) InP substrates. , 0, , . | | 0 |
| 138 | Effect of (GaP)/sub m/(InP)/sub m/ short period binary superlattice period on quantum wire formation by strain induced lateral layer ordering in GaInP/AlInP multi-quantum-wire lasers. , 0, , . | | 0 |
| 139 | Step Flow Surface Morphology in Plasma Assisted Molecular Beam Epitaxy Grown GaN. Materials Research Society Symposia Proceedings, 2000, 639, 3331. | 0.1 | 0 |
| 140 | Quasi-free standing GaN epitaxial layer grown on nano-columnar GaN by RF-plasma assisted molecular beam epitaxy. , 0, , . | | 0 |
| 141 | Yellow-green lasing emission from ZnCdSe/BeZnTe II-VI laser diodes on InP substrates. , 0, , . | | 0 |
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